



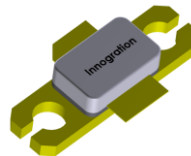
Gallium Nitride 28V 60W, RF Power Transistor

Description

The GTAH35061GX is a 60W internally matched, GaN HEMT, designed from 2 to 4.0GHz, especially 5G NR or LTE application, as well as either Pulse or CW application

There is no guarantee of performance when this part is used in applications designed Outside of these frequencies.

GTAH35061GX



- Typical performance (on narrow band fixture with device soldered)

$V_{DD}=28V$ $I_{DQ}=10mA$, CW

Freq	P1dB	P1dB	P1dB Eff	P1dB Gain	P3dB	P3dB	P3dB Eff
(MHz)	(dBm)	(W)	%	dB	(dBm)	(W)	%
3300	47.83	60.7	61.2	16.73	48.55	71.7	64.8
3400	47.25	53.1	59.6	17.33	48.4	69.2	65.1
3500	46.63	46.0	58.2	17.03	47.97	62.7	65.0

Recommended driver: GTAH80004PD

Applications and Features

- Suitable for wireless communication infrastructure, wideband amplifier, EMC testing, ISM etc.
- High Efficiency and Linear Gain Operations
- Thermally Enhanced Industry Standard Package
- High Reliability Metallization Process
- Excellent thermal Stability and Excellent Ruggedness
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Important Note: Proper Biasing Sequence for GaN HEMT Transistors

Turning the device ON

1. Set VGS to the pinch-off (VP) voltage, typically -5 V
2. Turn on VDS to nominal supply voltage (28V)
3. Increase VGS until IDS current is attained
4. Apply RF input power to desired level

Turning the device OFF

1. Turn RF power off
2. Reduce VGS down to VP, typically -5 V
3. Reduce VDS down to 0 V
4. Turn off VGS

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DS}	150	Vdc
Gate--Source Voltage	V_{GS}	-10,+2	Vdc
Operating Voltage	V_{DD}	36	Vdc
Maximum Forward Gate Current @ $T_C = 25^{\circ}C$	I_{gmax}	14	mA
Storage Temperature Range	T_{stg}	-65 to +150	$^{\circ}C$
Case Operating Temperature	T_C	+150	$^{\circ}C$
Operating Junction Temperature(See note 1)	T_J	+225	$^{\circ}C$
Total Device Power Dissipation (Derated above $25^{\circ}C$, see note 2)	P_{diss}	70	W

Note: 1. Continuous operation at maximum junction temperature will affect MTTF

2. Bias Conditions should also satisfy the following expression: $P_{diss} < (T_J - T_C) / R_{JC}$ and $T_C = T_{case}$



Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_C = 85^{\circ}\text{C}$, $T_J = 200^{\circ}\text{C}$, RF CW operation	$R_{\theta JC}$	1.7	C/W

Table 3. Electrical Characteristics ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = -8\text{V}$; $I_{DS} = 14\text{mA}$	V_{DSS}	150			V
Gate Threshold Voltage	$V_{DS} = 28\text{V}$, $I_D = 14\text{mA}$	$V_{GS(th)}$	-4		-2	V
Gate Quiescent Voltage	$V_{DS} = 28\text{V}$, $I_{DS} = 100\text{mA}$, Measured in Functional Test	$V_{GS(Q)}$		-2.5		V

Typical performance

3.3-3.5GHz

Figure 2: Small signal gain and return loss Vs Frequency

$V_{DS} = 28\text{V}$, $I_{DQ} = 100\text{mA}$, input power = 0dBm

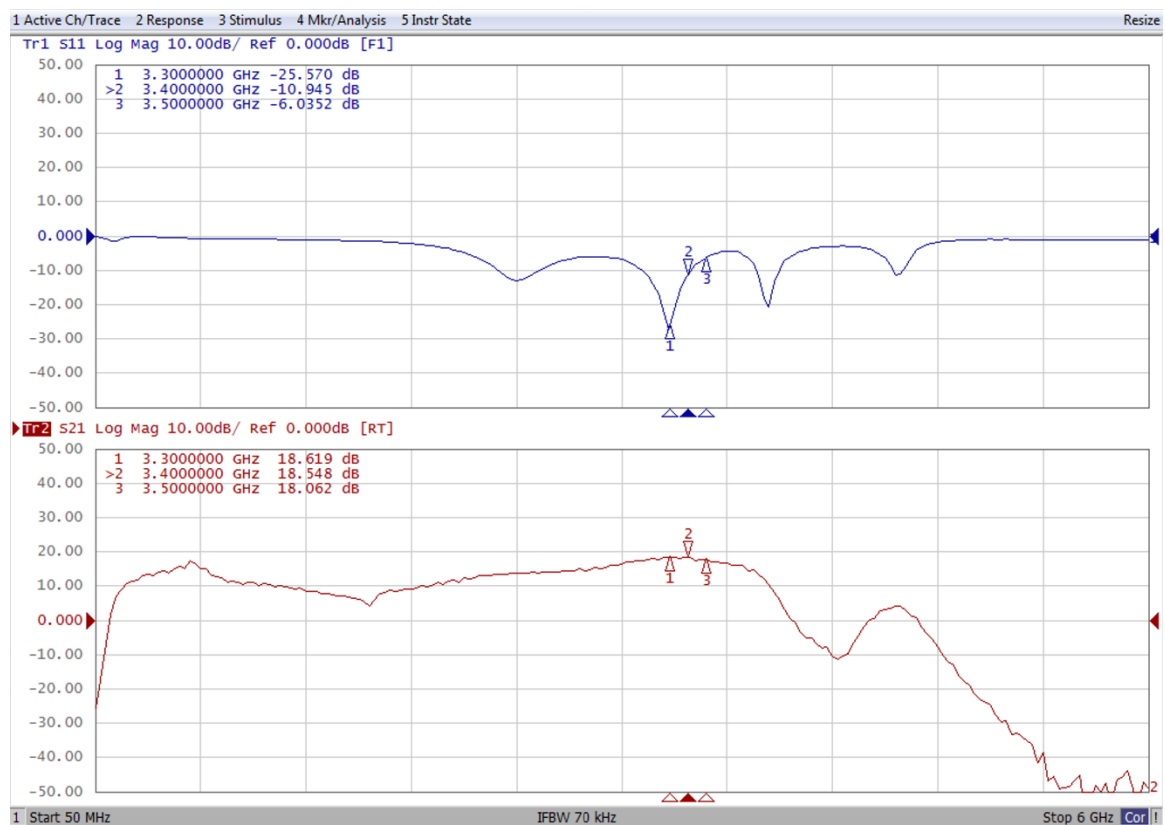


Figure 3: Efficiency and power gain as function of Pout

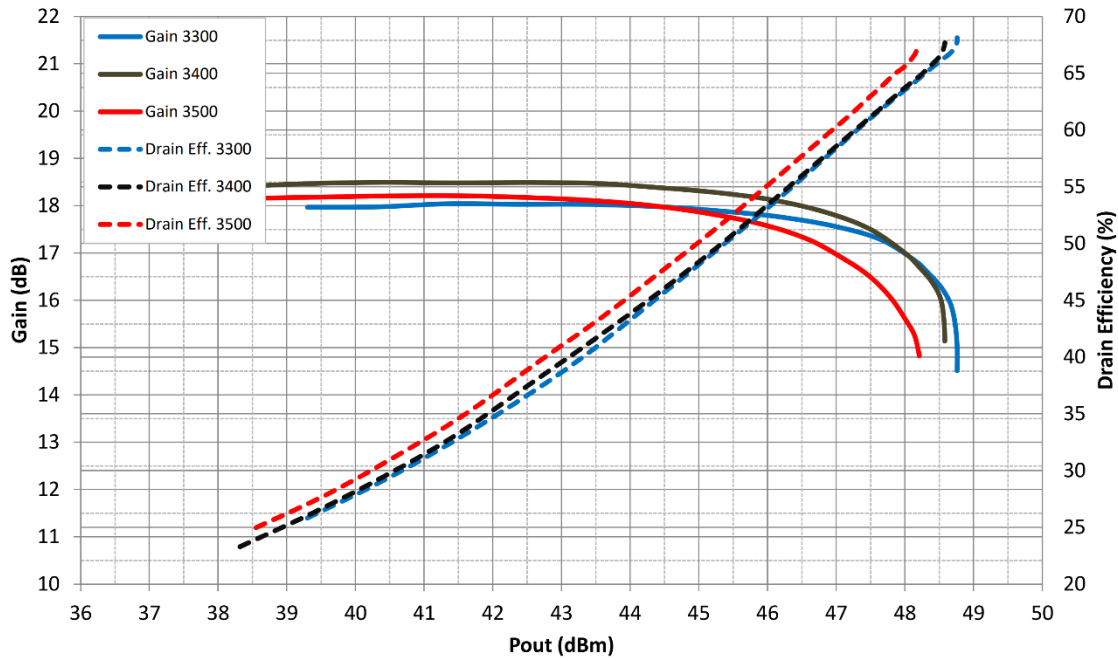
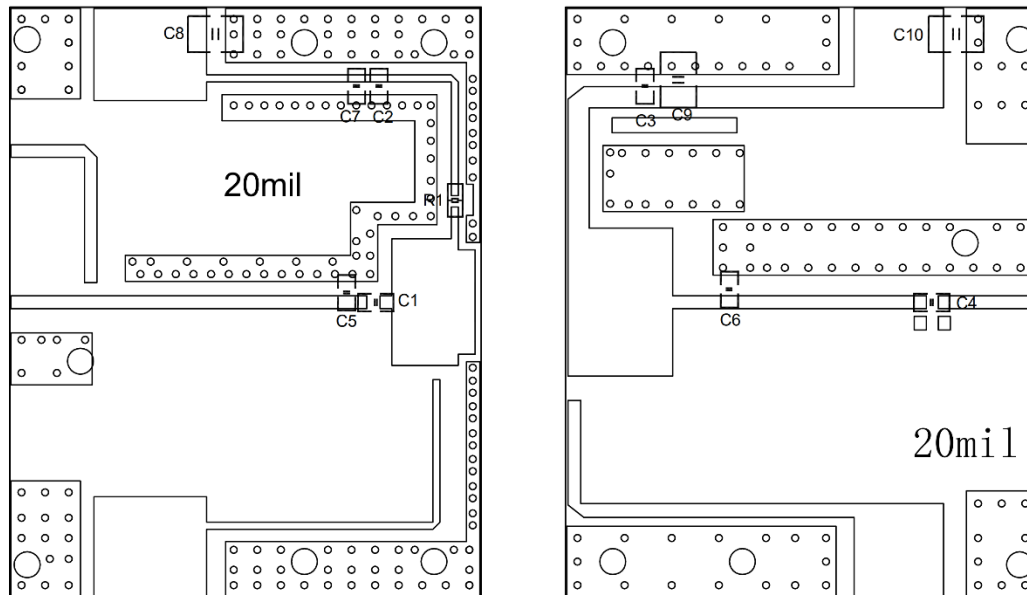


Figure 4: Picture and Bill of materials of application circuit
(Layout Gerber file upon request, 20mils RO4350B)



Reference	Footprint	Value	Quantity
C1, C2, C3, C4	0603	10pF/250V	4
C5	0603	1.2pF/250V	1
C6	0603	0.6pF/250V	1
C7	0603	0.1uF/16V	1
C8, C9, C10	1210	10uF/100V	3
R1	0603	10R	1
	G2	GTAH35061G2	1



Package Outline

Flanged ceramic package; 2 leads

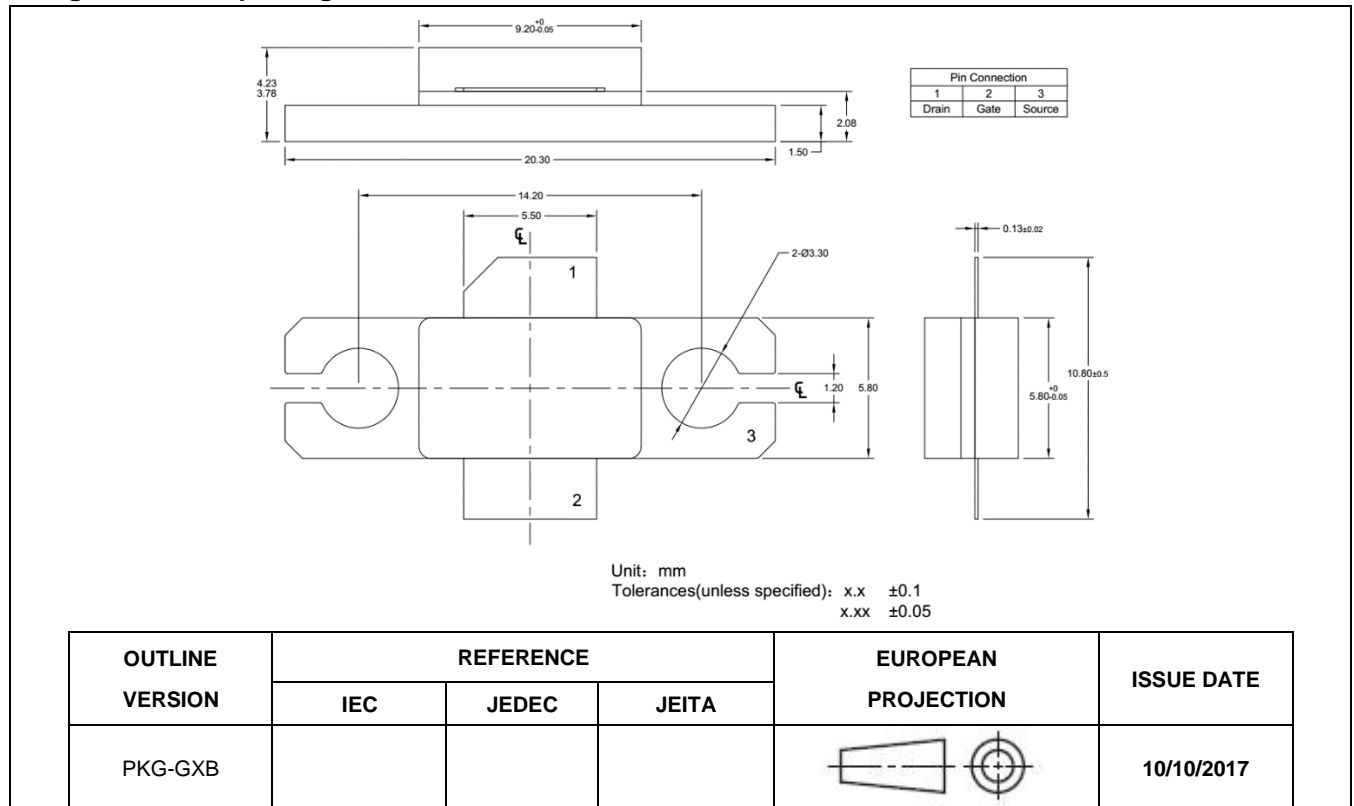


Figure 1. Package Outline PKG-G2E



Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2024/8/28	V1.0	Preliminary Datasheet Creation

Application data based on ZBB-24-31

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